




	<p>SI7882DP-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI7882DP-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET N-CH 12V 13A PPAK SO-8</p>
<p>Image may be representation. See specs for product details.</p>	<p>Datenblätter:  SI7882DP-T1-GE3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, 3000 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

Spezifikationen

Teilenummer	SI7882DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 12V 13A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	3000 pcs Stock
detaillierte Beschreibung	N-Channel 12V 13A (Ta) 1.9W (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	1.9W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	13A (Ta)
Rds On (Max) @ Id, Vgs	5.5 mOhm @ 17A, 4.5V
VGS (th) (Max) @ Id	1.4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	30nC @ 4.5V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7882DP-T1-GE3CT

SI7882DP-T1-GE3 ist neu im Original, Suche SI7882DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7882DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7882DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7884BDP-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 58A PPAK SO-8</p>	 <p>SI7884BDP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 58A PPAK SO-8</p>	 <p>SI7882DP VISHAY SI7882DP VISHAY</p>	 <p>SI7882DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 12V 13A PPAK SO-8</p>
 <p>SI7884BDP-T1-E3 Vishay / Siliconix MOSFET N-CH 40V 58A PPAK SO-8</p>	 <p>SI7884BDP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 58A PPAK SO-8</p>	 <p>SI7882DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 12V 13A PPAK SO-8</p>	 <p>SI7882DP-T1-E3 Vishay / Siliconix MOSFET N-CH 12V 13A PPAK SO-8</p>

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| <ul style="list-style-type: none"> ⊛ SI7866DP-T1 ⊣ SI7868ADP-T1-E3 ⊛ SI7868DP-T1-GE3 D SI7872DP-T1-E3 ⇒ SI7880ADP-T1-GE3 ↔ SI7882DP-T1-GE3 ⊛ SI7884BDP-T1-GE3 ⊣ SI7886ADP-T1-GE3 ⊛ SI7886DP-T1-GE3 ↔ SI7892ADP-T1-E3 | <ul style="list-style-type: none"> ↔ SI7866DP-T1-E3 ⊛ SI7868ADP-T1-GE3 ⊣ SI786LG-T1 ⊛ SI7872DP-T1-GE3 ↔ SI7880ADP-T1-GE3 ⇒ SI7884BDP D SI7884DP-T1-E3 ⊛ SI7886ADP-T1-GE3 ⊣ SI7888DP-T1-E3 ⊛ SI7892ADP-T1-GE3 | <ul style="list-style-type: none"> ⇒ SI7866DP-T1-GE3 D SI7868ADP-T1-GE3 ⊛ SI786LG-T1-E3 ⊣ SI7872DP-T1-GE3 ⊛ SI7880DP-T1-GE3 D SI7884BDP-T1-E3 ⇒ SI7884DP-T1-GE3 ↔ SI7886DP ⊛ SI7888DP-T1-E3 ⊣ SI7892ADP-T1-GE3 | <ul style="list-style-type: none"> D SI7868ADP ⇒ SI7868DP-T1 ↔ SI7872DP ⊛ SI7880ADP-T1-E3 ⊣ SI7882DP-T1-E3 ⊛ SI7884BDP-T1-E3 ↔ SI7886ADP-T1-E3 ⇒ SI7886DP-T1 D SI7888DP-T1-GE3 ⊛ SI7892BDP-T1-E3 | <ul style="list-style-type: none"> ⇒ SI7868ADP-T1-E3 ⇒ SI7868DP-T1-E3 ⇒ SI7872DP-T1-E3 ⇒ SI7880ADP-T1-E3 ⇒ SI7882DP-T1-E3 ⊣ SI7884BDP-T1-GE3 ⇒ SI7886ADP-T1-E3 ⇒ SI7886DP-T1-E3 ⇒ SI7888DP-T1-GE3 ⇒ SI7892BDP-T1-E3 |
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